

**TOSHIBA**

**2SK2550**

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSV)

# 2SK2550

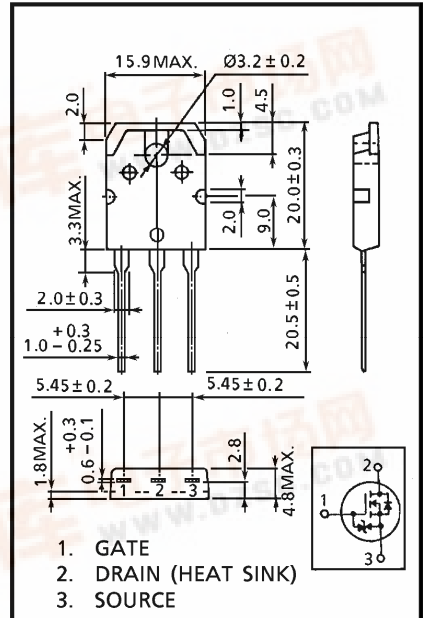
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

INDUSTRIAL APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 24\text{ m}\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 27\text{ S}$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 100\text{ }\mu\text{A}$  (Max.) ( $V_{DS} = 50\text{ V}$ )
- Enhancement-Mode :  $V_{th} = 1.5\sim 3.5\text{ V}$   
( $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$ )



JEDEC	—
EIAJ	SC-65
TOSHIBA	2-16C1B

Weight : 4.6 g

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Drain-Source Voltage	$V_{DSS}$	50	V	
Drain-Gate Voltage ( $R_{GS} = 20\text{ k}\Omega$ )	$V_{DGR}$	50	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Drain Current	DC	$I_D$	45	A
	Pulse	$I_{DP}$	135	A
Drain Power Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	100	W	
Single Pulse Avalanche Energy**	$E_{AS}$	115	mJ	
Avalanche Current	$I_{AR}$	45	A	
Repetitive Avalanche Energy*	$E_{AR}$	10	mJ	
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$	
Storage Temperature Range	$T_{stg}$	$-55\sim 150$	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.25	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ\text{C/W}$

Note ;

\* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

\*\*  $V_{DD} = 25\text{ V}, T_{ch} = 25^\circ\text{C}$  (initial),  $L = 71\text{ }\mu\text{H}, R_G = 25\text{ }\Omega, I_{AR} = 45\text{ A}$

**This transistor is an electrostatic sensitive device.**

**Please handle with caution.**

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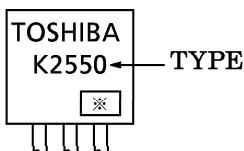
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	50	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	24	30	$\text{m}\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	15	27	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$	—	1250	—	pF
Reverse Transfer Capacitance		$C_{rss}$		—	250	—	
Output Capacitance		$C_{oss}$		—	700	—	
Switching Time	Rise Time	$t_r$	<p><math>V_{GS} = 10\text{ V}</math> <math>V_{GS} = 0\text{ V}</math> <math>I_D = 25\text{ A}</math> <math>R_L = 1.2\ \Omega</math> <math>V_{DD} \doteq 30\text{ V}</math></p>	—	20	—	ns
	Turn-on Time	$t_{on}$		—	30	—	
	Fall Time	$t_f$		—	40	—	
	Turn-off Time	$t_{off}$		$V_{IN} : t_r, t_f < 5\text{ ns},$ $\text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$	—	120	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} \doteq 40\text{ V}, V_{GS} = 10\text{ V}$ $I_D = 45\text{ A}$	—	36	—	nC
Gate-Source Charge		$Q_{gs}$		—	22	—	
Gate-Drain (“Miller”) Charge		$Q_{gd}$		—	14	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	45	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	135	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$ $dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	75	—	ns
Reverse Recovery Charge	$Q_{rr}$		—	75	—	nC

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)